

ABSTRACT OF DISCLOSURE

A method of reducing notching during reactive ion etching (RIE) is provided.

The method is useful when RIE is performed to pass through a silicon layer on a multi-layered structure on which the silicon layer, an insulating layer and a silicon

- 5 substrate are sequentially deposited. The method includes the steps of: forming an insulating layer on a silicon substrate; forming trenches on the insulating layer to expose the silicon substrate; forming a silicon layer on the insulating layer to fill the trenches; and patterning the silicon layer to form first etch regions, which pass through the silicon layer, to include the trenches. According to the method, it is
- 10 possible to remarkably reduce notching without depositing a metal layer, when a multi-layered structure including a silicon layer which is etched to be passed through during RIE is fabricated.